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P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A) ^a	Q _g (Typ.)		
-30	37 at V _{GS} = -10 V	F.C.	14 nC		
	62 at V _{GS} = -4.5 V	- 5.6			

FEATURES • DT-Trench

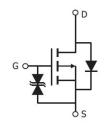
- DT-Trench Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC
- Gate-Source ESD Protected



RoHS

APPLICATIONS

- Load Switch
- · Notebook Adaptor Switch
- DC/DC Converter



P-Channel MOSFET

D	3
1 G	2 s

(SOT-23-3L)

Top View
DTS3401A

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherw
Parameter
Drain-Source Voltage

Parameter			Limit	Unit	
Drain-Source Voltage			- 30	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	I _D	- 5.6	A	
	T _C = 70 °C		- 4.9		
	T _A = 25 °C		- 4.2 ^{a, b}		
	T _A = 70 °C		- 3.3 ^{a, b}		
Pulsed Drain Current			-25		
Continuous Source-Drain Diode Current	T _C = 25 °C	I _S	- 2.1		
Continuous Source-Diain Diode Current	T _A = 25 °C	'S	- 1 ^{a, b}	,	
	T _C = 25 °C		2.5		
Maximum Power Dissipation	T _C = 70 °C	P _D	1.6	w	
Maximum Power Dissipation	T _A = 25 °C		1.25 ^{a, b}		
	T _A = 70 °C	1	0.8 ^{a, b}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{c, d}	t ≤ 5 s	R _{thJA}	75	100	°C/W	
Maximum Junction-to-Foot	Steady State	R _{thJF}	40	50		

Notes

- a. Based on $T_C = 25$ °C.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. Maximum under Steady State conditions is 166 °C/W.

Rev.1.0



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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static					*		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, } I_{D} = -250 \mu\text{A}$	- 30			V	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		-3	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zara Cata Valtaria Drain Comment	I _{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	μА	
Zero Gate Voltage Drain Current		V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 55 °C			- 5		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	-10			Α	
D : 0		V _{GS} = - 10 V, I _D = - 4.2 A		37	53	mΩ	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 3.2 A		62	70		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 4.2 A		10		S	
Dynamic ^b							
Input Capacitance	C _{iss}			610			
Output Capacitance	Coss	V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz		475		pF	
Reverse Transfer Capacitance	C _{rss}	1		370			
Total Gate Charge	Q_q			14			
Gate-Source Charge	Q _{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -4.2 \text{ A}$		4		nC	
Gate-Drain Charge	Q _{gd}	-		6			
Gate Resistance	R _q	f = 1 MHz		5		Ω	
Turn-On Delay Time	t _{d(on)}			28			
Rise Time	t _r	$V_{DD} = -15 \text{ V}, R_{L} = 4.5 \Omega$		24			
Turn-Off DelayTime	t _{d(off)}	$I_D \cong -4.2 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		15			
Fall Time	t _f	1		9			
Turn-On Delay Time	t _{d(on)}			8		ns -	
Rise Time	t _r	$V_{DD} = -15 \text{ V}, R_L = 4.5 \Omega$		10			
Turn-Off DelayTime	t _{d(off)}	$I_D \cong -4.2 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		16			
Fall Time	t _f	1		8			
Drain-Source Body Diode Characteris	tics						
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			- 4.2		
Pulse Diode Forward Current	I _{SM}				-25	Α	
Body Diode Voltage	V _{SD}	I _S = -1 A, V _{GS} = 0 V		-0.6	-1	٧	
Body Diode Reverse Recovery Time	t _{rr}			15	25	ns	
Body Diode Reverse Recovery Charge	Q _{rr}	1		9	18	nC	
Reverse Recovery Fall Time	$\Gamma = -4.2 \text{ A dI/d}$			10			
Reverse Recovery Rise Time	t _b	†		8		ns	

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

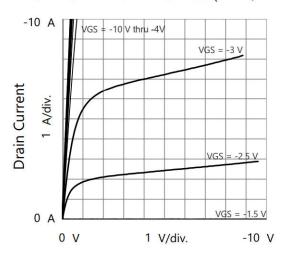
a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

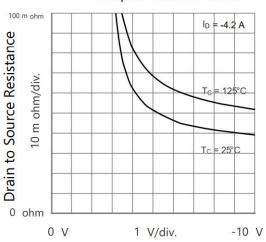


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

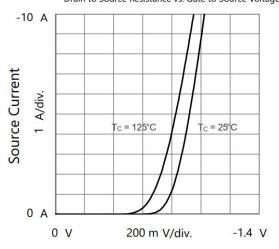
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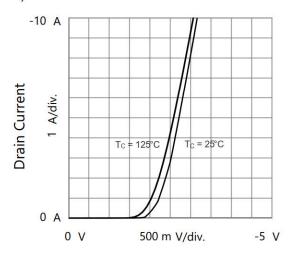
Drain to Source Voltage Output Characteristics



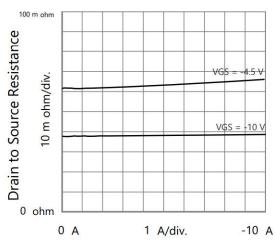
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



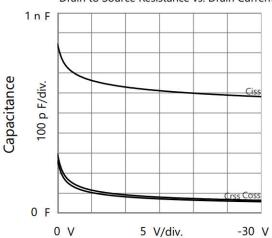
Source to Drain Voltage Body Diode Forward Characteristics



Gate to Source Voltage Transfer Characteristics



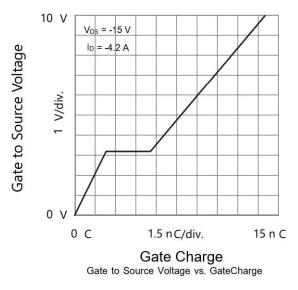
Drain Current
Drain to Source Resistance vs. Drain Current

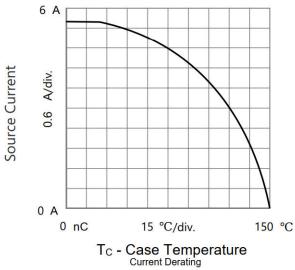


Drain to Source Voltage Capacitances

TYPICAL CHARACTERISTICS (25 C, unless otherwise noted)

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100 A

100 A

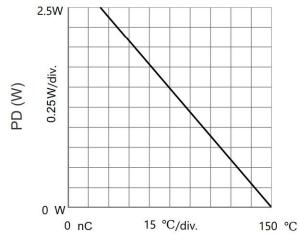
100 S

100 V

100 V

100 V

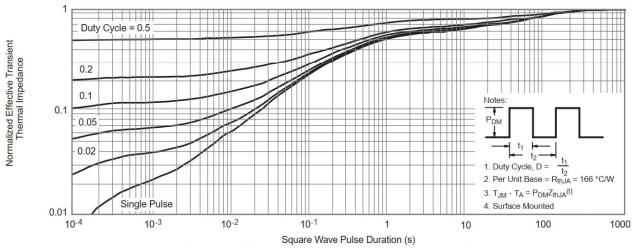
Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



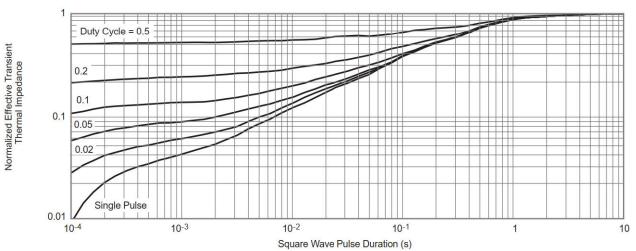
T_C - Case Temperature Power Derating



TYPICAL CHARACTERISTICS (25 C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot





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